

Appl. No. 10/030,867
Resp. Dated April 10, 2007
Reply to Office Action of February 13, 2007

Attorney Docket No. 81839.0105
Customer No. 26021

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Masanori KIMURA

Serial No: 10/030,867

Confirmation No.: 8937

Filed: April 29, 2002

For: METHOD FOR GROWING SINGLE
CRYSTAL OF SEMICONDUCTOR

Art Unit: 1722

Examiner: G. Nagesh Rao

**COMMENTS ON STATEMENT OF REASONS
FOR ALLOWANCE**

Mail Stop ISSUE FEE
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Applicant has received a Notice of Allowance, mailed February 13, 2007, together with a Notice of Allowability, for the above-identified Application. The Notice of Allowability includes Reasons for Allowance which appear on pages 2 and 3 thereof. Applicant wishes to make the following comments with respect to the Reasons for Allowance.

In the paragraph at the top of page 3 it is stated "Nowhere is it found in the prior art that this critical step occurs before the growing of the raw material melt prior to 60%." This is incorrect inasmuch as the critical step occurs after (and not "before") the growing of the raw material melt of 60% or more. Moreover, the growing of the raw material melt is of 60% or more (and not "prior to 60%).

I hereby certify that this correspondence is being transmitted via electronic filing on the date indicated below to:

Mail Stop Issue Fee
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

April 10, 2007

Rebecca Maiden

Name
Rebecca Maiden 04/10/07
Signature Date

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Consequently, the sentence at the top of page 3 should read "Nowhere is it found in the prior art that this critical step occurs after the growing of the raw material melt of 60% or more".

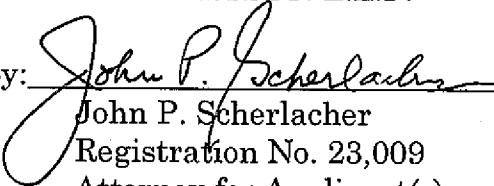
In the first line of the second paragraph on page 3, the prior art cited by the Examiner does not explicitly teach nor suggest (not "obviate") this critical limitation. Therefore, the first sentence of this paragraph should read "The prior art cited by Examiner does not explicitly teach nor suggest this critical limitation in the method for growing a semiconductor single crystal".

Further down in the second paragraph on page 3 (lines 5 and 6 of the second paragraph), the disclosure referred to is as noted by claim rejections (and not "noted by applicant's remarks"). Therefore, the appropriate parts of lines 5 and 6 of the second paragraph should read "...and as noted by claim rejections the combination of the Kojima, Ito, and Schupp references ...".

It is respectfully requested that the Examiner review and approve the changes noted by these comments.

Respectfully submitted,
HOGAN & HARTSON L.L.P.

Date: April 10, 2007

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